

# RICOH

## LOW RIPPLE VOLTAGE REGULATOR WITH EXTERNAL TRANSISTOR

### RN5RF SERIES

#### OUTLINE

The RN5RF Series are voltage regulator ICs which control external driver transistors with high ripple rejection, high accuracy output voltage, low supply current by CMOS process. Each of these voltage regulator ICs consists of a voltage reference unit, an error amplifier, output voltage setting resistor, short circuit current limiting circuit and chip enable circuit. These ICs are suitable for constructing regulators with ultra low dropout voltage and an output current in the range of several tens of mA and several hundreds mA. In addition to low supply current by CMOS process, chip enable function can be used to conserve battery life during standby.

Furthermore, a supreme ripple rejection and a transient response are suited for portable communication such as cell phones, PDAs, walky talkies. SOT23-5 (Mini Mold) package is available.

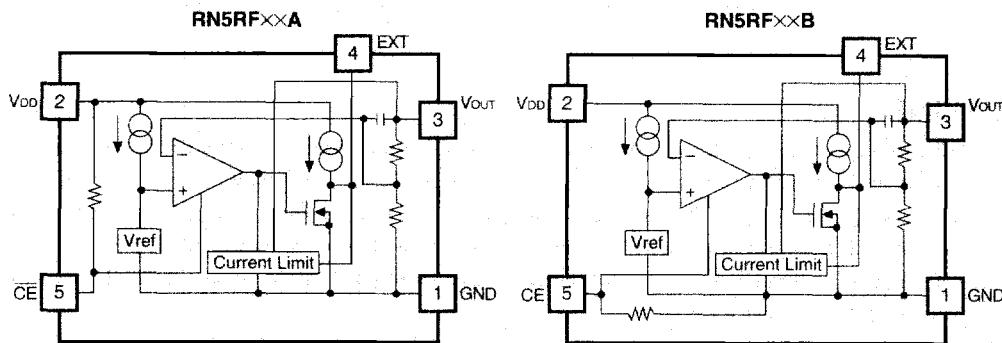
#### FEATURES

- Ultra Low Supply Current ..... TYP. 30 $\mu$ A
- Standby Mode ..... TYP. 0.1 $\mu$ A
- High Accuracy Output Voltage .....  $\pm 2.0\%$
- High Ripple Rejection ..... TYP. 60dB/ $f=1$ kHz
- Low Dropout Voltage ..... TYP. 0.1V/ $I_{OUT}=100$ mA, dependent on External Tr.
- Low Temperature Drift ..... TYP.  $\pm 100$ ppm/ $^{\circ}$ C
- High Line Regulation ..... TYP. 0.05%/V
- Output Voltage ..... Stepwise setting with a step of 0.1V in the range of 2.0V to 6.0V
- Current Limit for external Tr. ..... TYP. 8mA, Limit a base current

#### APPLICATIONS

- Power source for battery-powered equipment
- Telecommunications, Cameras, VCRs
- Power source for domestic appliances

## BLOCK DIAGRAM



## SELECTION GUIDE

The output voltage, the chip enable active type, the packing type and the taping type for the ICs can be selected at the user's request.

The selection can be made by designating the part number as shown below:

RN5RF xxxxx-xx ← Part Number

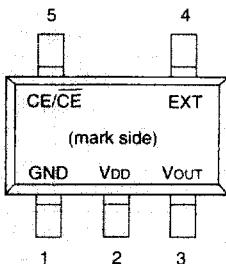
↑ ↑ ↑

a b c d

Code	Contents
a	Setting Output Voltage (VOUT): Stepwise setting with a step of 0.1V in the range of 2.0V to 6.0V is possible.
b	Designation of Chip enable Active Type A : "L" active type B : "H" active type
c	Designation of Packing type A : Taping C : Antistatic bag only for samples
d	Designation of Taping type Ex. TR, TL (refer to Taping Specifications, TR type is prescribed as a standard.)

## PIN CONFIGURATION

• SOT-23-5



## PIN DESCRIPTION

Pin No.	Symbol	Pin Description
1	GND	Ground Pin
2	VDD	Input Pin
3	VOUT	Output Pin
4	EXT	External Transistor Drive Pin (CMOS Output)
5	CE or $\overline{CE}$	Chip Enable Pin

## ABSOLUTE MAXIMUM RATINGS

Symbol	Item	Rating	Unit
V <sub>IN</sub>	Input Voltage	12	V
V <sub>CE</sub>	Input Voltage for CE/ $\overline{CE}$ Pin	-0.3 to V <sub>IN</sub> +0.3	V
V <sub>EXT</sub>	EXT Output Voltage	12	V
I <sub>EXT</sub>	EXT Output Current	50	mA
P <sub>D</sub>	Power Dissipation	150	mW
T <sub>opt</sub>	Operating Temperature Range	-40 to +85	°C
T <sub>stg</sub>	Storage Temperature Range	-55 to +125	°C

### ABSOLUTE MAXIMUM RATINGS

Absolute Maximum ratings are threshold limit values that must not be exceeded even for an instant under any conditions. Moreover, such values for any two items must not be reached simultaneously. Operation above these absolute maximum ratings may cause degradation or permanent damage to the device. These are stress ratings only and do not necessarily imply functional operation below these limits.

## ELECTRICAL CHARACTERISTICS

### • RN5RF××A

Topt=25°C

Symbol	Item	Conditions	MIN.	TYP.	MAX.	Unit
VOUT	Output Voltage	VIN-VOUT=1.0V IOUT=50mA	VOUT ×0.98		VOUT ×1.02	V
IOUT	Output Current	VIN-VOUT=1.0V		1*1		A
IEXT	EXT Current	VIN=4.0V, VEXT=2.0V	5	8	15	mA
$\Delta V_{\text{OUT}}$ $\Delta I_{\text{OUT}}$	Load Regulation	VIN-VOUT=1.0V 1mA ≤ IOUT ≤ 100mA	-60		60	mV
VDF	Dropout Voltage	IOUT=100mA		0.1	0.2	V
Iss	Supply Current	VIN-VOUT=1.0V IOUT=0mA		30	50	μA
Istandby	Standby Current	VIN=10.0V	0.01	0.1	1.0	μA
IEXTleak	EXT Leakage Current				0.5	μA
$\Delta V_{\text{OUT}}$ $\Delta V_{\text{IN}}$	Line Regulation	IOUT=50mA VOUT+0.5V ≤ VIN ≤ 10V	0	0.05	0.30	%/V
RR	Ripple Rejection	f=1kHz, sinusoidal 0.5Vp-p VIN-VOUT=1.0V		60		dB
VIN	Input Voltage				10	V
VEXT	EXT Output Voltage				10	V
$\Delta V_{\text{OUT}}$ $\Delta T_{\text{opt}}$	Output Voltage Temperature Coefficient	IOUT=10mA -40°C ≤ Topt ≤ 85°C		±100		ppm/°C
RPU	Pull up resistance for CE pin			4		MΩ
VCEH	CE Input Voltage "H"		1.5		VIN	V
VCEL	CE Input Voltage "L"		0		0.25	V

\*1) The output current depends on the performance of external PNP transistor. Use External PNP transistor of a low saturation type, with an hFE between 100 and 300.

\* ) With respect to Test Circuit, refer to Typical Application.

## • RN5RFxxB

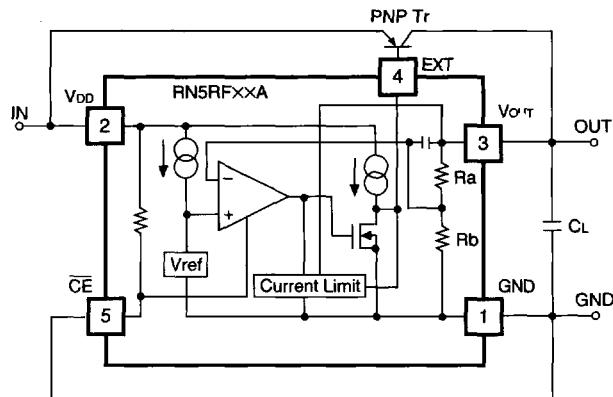
Topt=25°C

Symbol	Item	Conditions	MIN.	TYP.	MAX.	Unit
VOUT	Output Voltage	VIN-VOUT=1.0V IOUT=50mA	VOUT ×0.98		VOUT ×1.02	V
IOUT	Output Current	VIN-VOUT=1.0V		1 <sup>*1</sup>		A
IEXT	EXT Current	VIN=4.0V, VEXT=2.0V	5	8	15	mA
$\frac{\Delta V_{\text{OUT}}}{\Delta I_{\text{OUT}}}$	Load Regulation	VIN-VOUT=1.0V 1mA ≤ IOUT ≤ 100mA	-60		60	mV
VDF	Dropout Voltage	IOUT=100mA		0.1	0.2	V
Iss	Supply Current	VIN-VOUT=1.0V IOUT=0mA		30	50	µA
Istandby	Standby Current	VIN=10.0V	0.01	0.1	1.0	µA
IEXTleak	EXT Leakage Current				0.5	µA
$\frac{\Delta V_{\text{OUT}}}{\Delta V_{\text{IN}}}$	Line Regulation	IOUT=50mA VOUT+0.5V ≤ VIN ≤ 10V	0	0.05	0.30	%/V
R <sub>R</sub>	Ripple Rejection	f=1kHz, sinusoidal 0.5Vp-p VIN-VOUT=1.0V		60		dB
VIN	Input Voltage				10	V
VEXT	EXT Output Voltage				10	V
$\frac{\Delta V_{\text{OUT}}}{\Delta T_{\text{opt}}}$	Output Voltage Temperature Coefficient	IOUT=10mA -40°C ≤ Topt ≤ 85°C		±100		ppm/°C
R <sub>PD</sub>	Pull down resistance for CE pin			4		MΩ
V <sub>CEH</sub>	CE Input Voltage "H"		1.5		V <sub>IN</sub>	V
V <sub>CEL</sub>	CE Input Voltage "L"		0		0.25	V

\*1) The output current depends on the performance of external PNP transistor. Use External PNP transistor of a low saturation type, with an hFE between 100 and 300.

\* ) With respect to Test Circuit, refer to Typical Application.

## OPERATION



In these ICs, Output Voltage  $V_{out}$  is detected by Feed-back Resistors,  $R_A$  and  $R_B$  and the detected Output Voltage is compared with a reference voltage by Error Amplifier so that the base current of External PNP Transistor can be adjusted and Output Voltage  $V_{out}$  is able to be regulated.

The base current of an external  $Tr.$  is monitored and controlled by an internal Base Current Limit circuit to keep current within a proper range. Furthermore, the other current limit circuit prevents a problem which is that a base current increases sharply when input Voltage  $V_{IN}$  becomes lower than Set Output Voltage.

### Notes on selecting external components

#### (1) On external PNP transistor

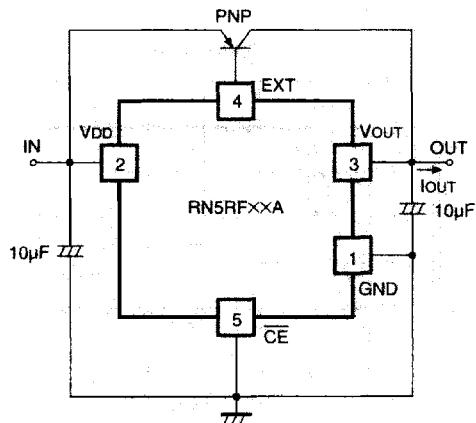
Be careful of output current, input voltage and power dissipation of External PNP Transistor.

It is said that External PNP Transistor with a low  $V_{CE}(\text{sat})$  and an  $hFE$  between 100 and 300 is suitable.

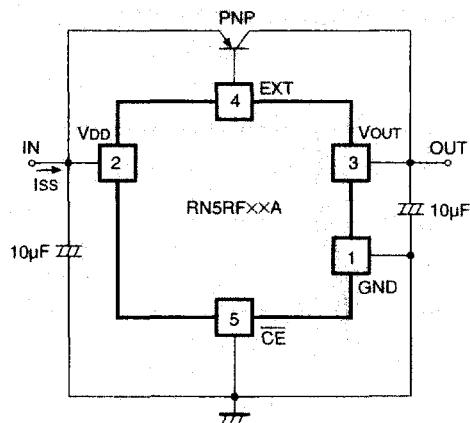
#### (2) On phase compensation

In these ICs, phase compensation is made for securing stable operation on the output stage even if the load current is varied. For this purpose, be sure to use a capacitor  $C_L$  (tantalum type) with a capacitance of  $10\mu F$  or more. There may be the case the loop oscillation takes place when a tantalum capacitor  $C_L$  with a large ESR is used, so select the  $C_L$  carefully including the frequency characteristics.

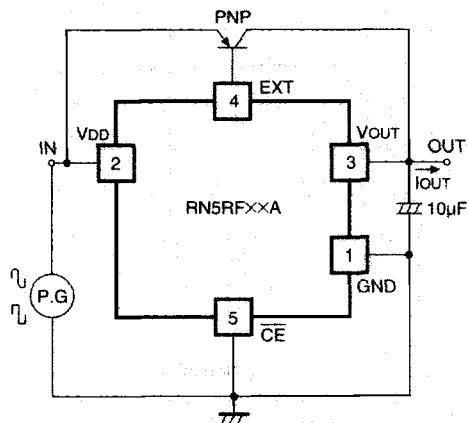
## TEST CIRCUITS



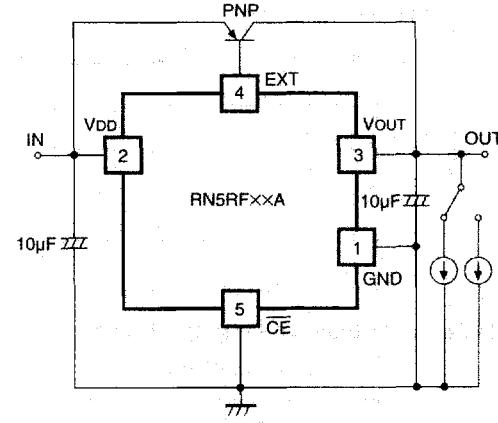
Basic Test Circuit



Test Circuit for Supply Current



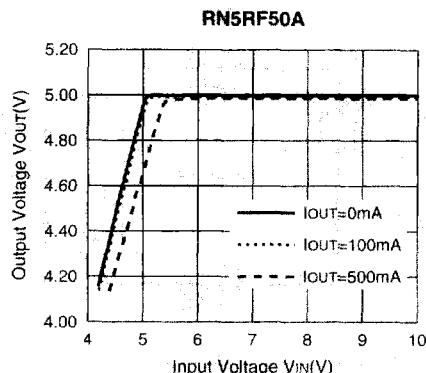
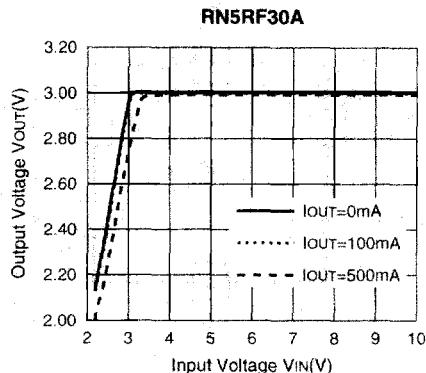
Test Circuit for Ripple Rejection and Line Transient Response



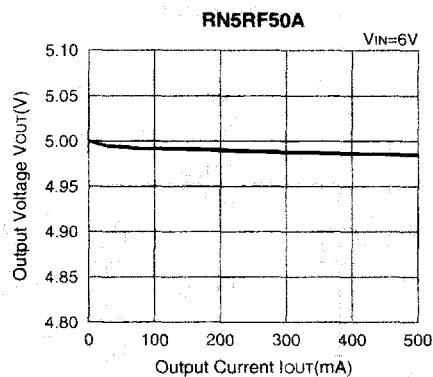
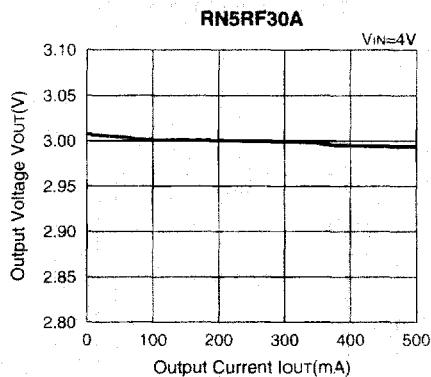
Test Circuit for Load Transient Response

## TYPICAL CHARACTERISTICS

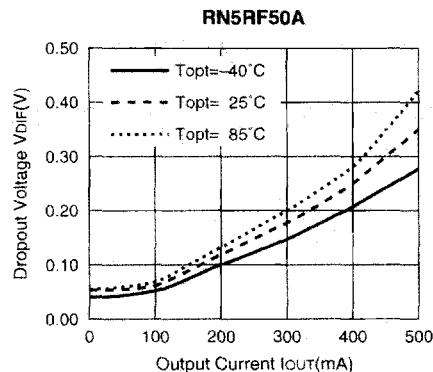
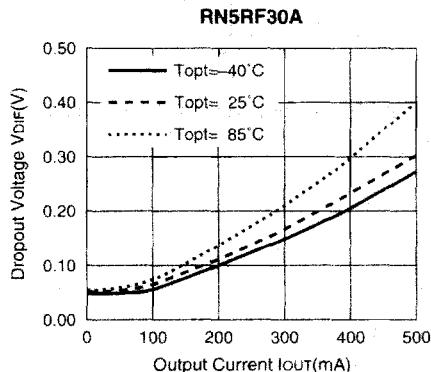
### 1) Output Voltage vs. Input Voltage ( $T_{opt}=25^{\circ}\text{C}$ )

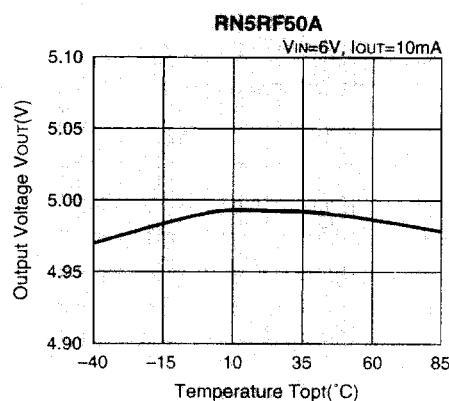
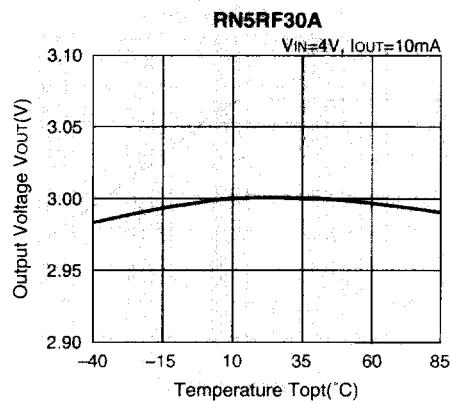
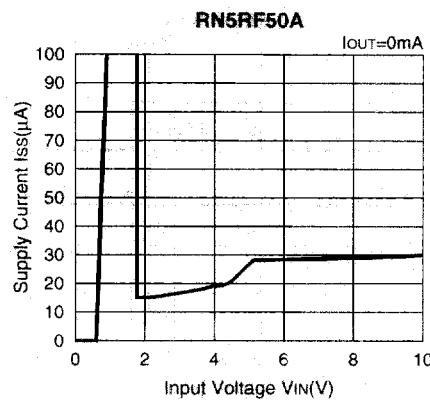
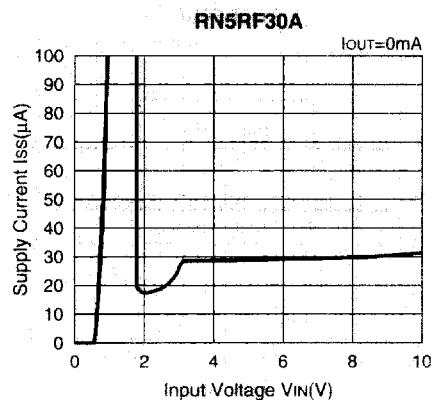
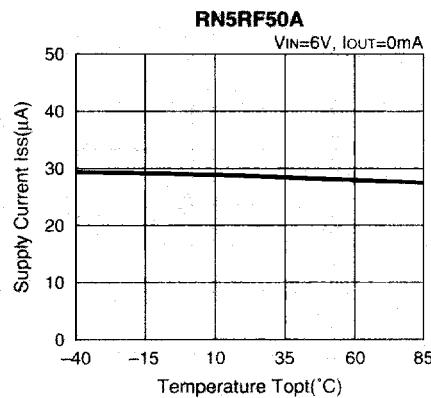
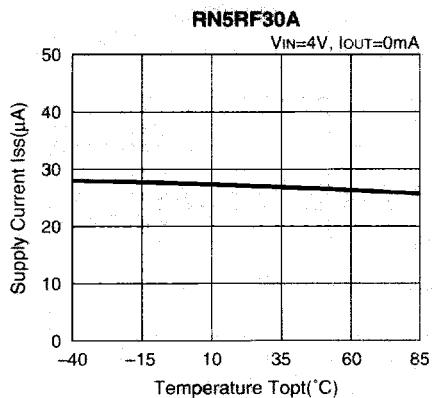


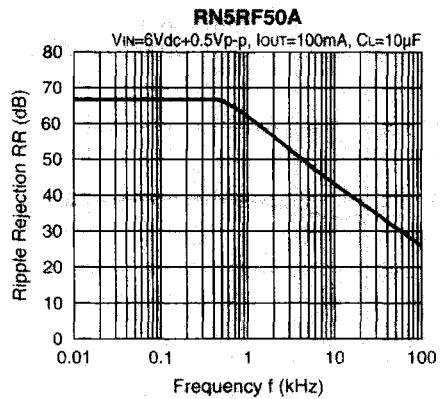
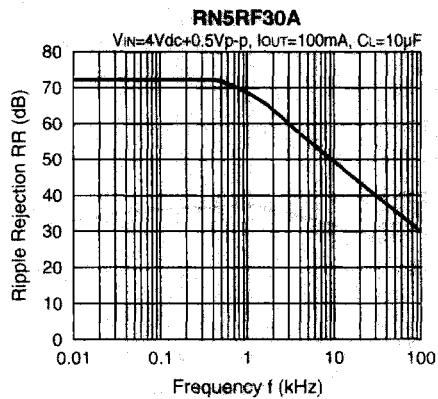
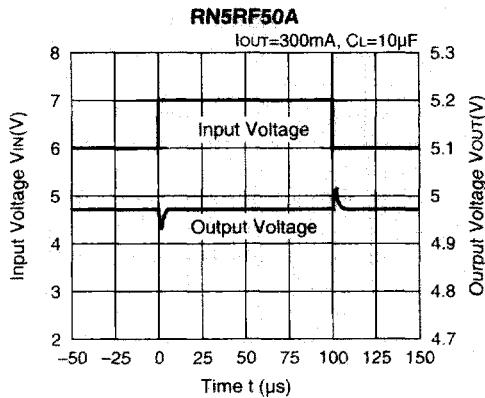
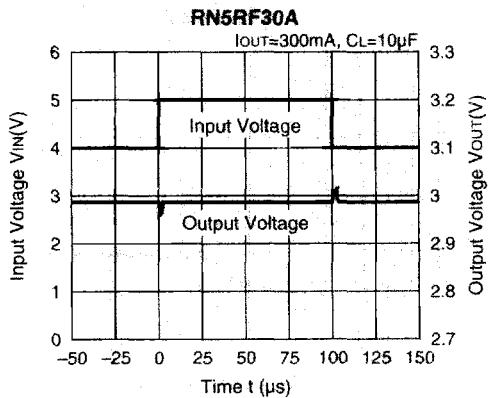
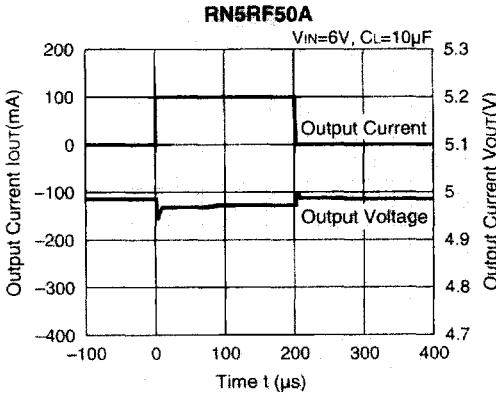
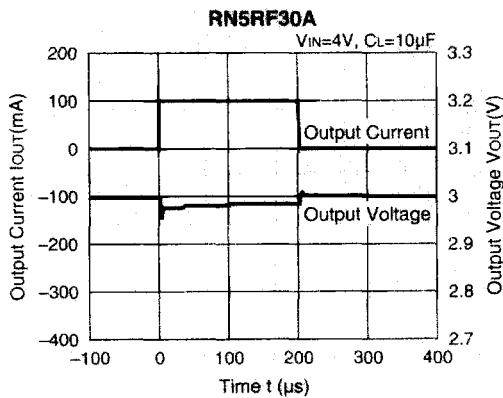
### 2) Output Voltage vs. Output Current ( $T_{opt}=25^{\circ}\text{C}$ )



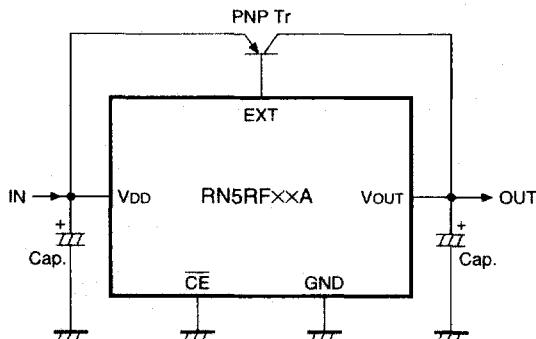
### 3) Dropout Voltage vs. Output Current



**4) Output Voltage vs. Temperature****5) Supply Current vs. Input Voltage (T<sub>opt</sub>=25°C)****6) Supply Current vs. Temperature**

7) Ripple Rejection vs. Frequency ( $T_{opt}=25^{\circ}\text{C}$ )8) Line Transient Response ( $T_{opt}=25^{\circ}\text{C}$ )9) Load Transient Response ( $T_{opt}=25^{\circ}\text{C}$ )

## TYPICAL APPLICATION



Parts    Transistor : 2SB766A  
           Capacitor : 10 $\mu$ F (tantalum type)

### APPLICATION HINTS

Using these ICs, be sure to take care of the following points:

- 1) Minimize the impedance of VDD and GND wiring. A large current flows through these wiring. When the wiring impedance is high, the operation of the ICs tends to be unstable and is vulnerable to noise.
- 2) Provide a capacitor with a capacitance of about 10 $\mu$ F (tantalum type) between VDD pin and GND pin with a minimum wiring length.
- 3) Rush current flows into the capacitor connected to the output of Regulators at the start of the operation of the Regulators. As these ICs are used with external PNP Transistor, the current drive performance of this Regulator is excellent. Therefore, when Regulator starts to operate, for example, under the conditions that hFE of External PNP Transistor is 100 and the base current of the limiter is 8mA, a rush current becomes 800mA.
- 4) In these ICs, phase compensation is made for securing stable operation on the output stage even if the load current is varied. For this purpose, be sure to use a capacitor CL (tantalum type) with a capacitance of 10 $\mu$ F or more. There may be the case the loop oscillation takes place when a tantalum capacitor Ct with a large ESR is used, so select the Ct carefully including the frequency characteristics.
- 5) Set external parts as close as possible to the IC and minimize the connection between the parts and the IC.